

4V Drive Nch + Pch MOSFET

QS8M12

● Structure

Silicon N-channel MOSFET/
Silicon P-channel MOSFET

● Features

- 1) Low on-resistance.
- 2) High power package(TSMT8).
- 3) Low voltage drive(4V drive).

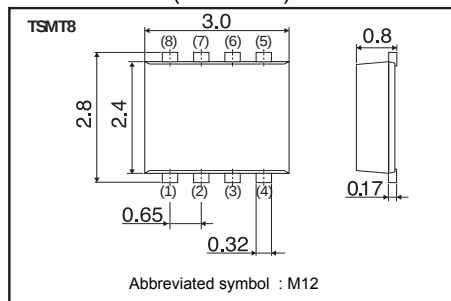
● Application

Switching

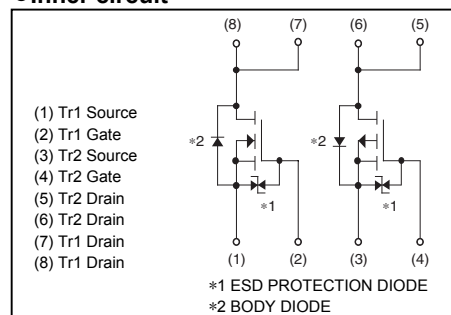
● Packaging specifications

Type	Package	Taping
	Code	TCR
	Basic ordering unit (pieces)	3000
QS8M12		○

● Dimensions (Unit : mm)



● Inner circuit



● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits		Unit
		Tr1 : N-ch	Tr2 : P-ch	
Drain-source voltage	V_{DS}	30	-30	V
Gate-source voltage	V_{GS}	±20	±20	V
Drain current	Continuous	I_D	±4	A
	Pulsed	I_{DP} *1	±12	A
Source current (Body Diode)	Continuous	I_S	1.0	A
	Pulsed	I_{SP} *1	12	A
Power dissipation	P_D *2	1.5		W / TOTAL
		1.25		W / ELEMENT
Channel temperature	T_{ch}	150		°C
Range of storage temperature	T_{stg}	-55 to +150		°C

*1 $P_w \leq 10\mu s$, Duty cycle $\leq 1\%$

*2 Mounted on a ceramic board.

● **Electrical characteristics** (Ta = 25°C)

<Tr1(Nch)>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	-	-	V	$I_D = 1mA, V_{GS} = 0V$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	1.0	-	2.5	V	$V_{DS} = 10V, I_D = 1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	30	42	m Ω	$I_D = 4A, V_{GS} = 10V$
		-	40	56		$I_D = 4A, V_{GS} = 4.5V$
		-	45	63		$I_D = 4A, V_{GS} = 4V$
Forward transfer admittance	$ Y_{fs} ^*$	2.5	-	-	S	$V_{DS} = 10V, I_D = 4A$
Input capacitance	C_{iss}	-	250	-	pF	$V_{DS} = 10V$
Output capacitance	C_{oss}	-	90	-	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	-	45	-	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	7	-	ns	$I_D = 2A, V_{DD} = 15V$
Rise time	t_r^*	-	30	-	ns	$V_{GS} = 10V$
Turn-off delay time	$t_{d(off)}^*$	-	30	-	ns	$R_L = 7.5\Omega$
Fall time	t_f^*	-	5	-	ns	$R_G = 10\Omega$
Total gate charge	Q_g^*	-	3.4	-	nC	$I_D = 4A, V_{DD} = 15V$
Gate-source charge	Q_{gs}^*	-	1.2	-	nC	$V_{GS} = 5V$
Gate-drain charge	Q_{gd}^*	-	1.3	-	nC	

*Pulsed

● **Body diode characteristics** (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^*	-	-	1.2	V	$I_s = 4A, V_{GS} = 0V$

*Pulsed

● **Electrical characteristics** (Ta = 25°C)

<Tr2(Pch)>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	-	-	V	$I_D = -1mA, V_{GS} = 0V$
Zero gate voltage drain current	I_{DSS}		-	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	-1.0	-	-2.5	V	$V_{DS} = -10V, I_D = -1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	40	56	m Ω	$I_D = -4A, V_{GS} = -10V$
		-	55	77		$I_D = -2A, V_{GS} = -4.5V$
		-	60	84		$I_D = -2A, V_{GS} = -4.0V$
Forward transfer admittance	$ Y_{fs} ^*$	3	-	-	S	$V_{DS} = -10V, I_D = -4A$
Input capacitance	C_{iss}	-	800	-	pF	$V_{DS} = -10V$
Output capacitance	C_{oss}	-	120	-	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	-	110	-	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	8	-	ns	$I_D = -2A, V_{DD} = -15V$
Rise time	t_r^*	-	20	-	ns	$V_{GS} = -10V$
Turn-off delay time	$t_{d(off)}^*$	-	80	-	ns	$R_L = 7.5\Omega$
Fall time	t_f^*	-	50	-	ns	$R_G = 10\Omega$
Total gate charge	Q_g^*	-	8.4	-	nC	$I_D = -4A, V_{DD} = -15V$
Gate-source charge	Q_{gs}^*	-	3.0	-	nC	$V_{GS} = -5V$
Gate-drain charge	Q_{gd}^*	-	3.5	-	nC	

*Pulsed

● **Body diode characteristics** (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^*	-	-	-1.2	V	$I_s = -4A, V_{GS} = 0V$

*Pulsed

●Electrical characteristic curves (Ta=25°C)

〈Tr.1(Nch)〉

Fig.1 Typical Output Characteristics (I)

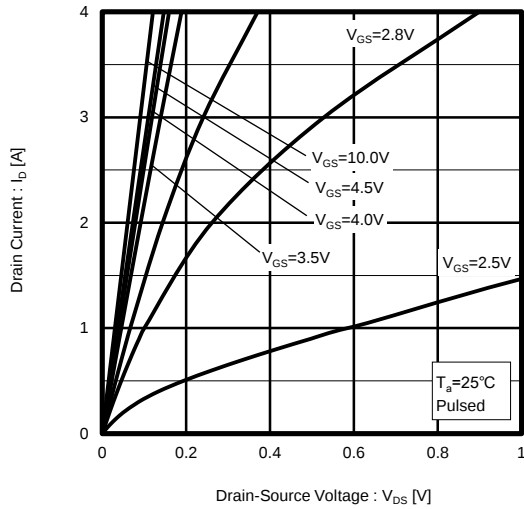


Fig.2 Typical Output Characteristics (II)

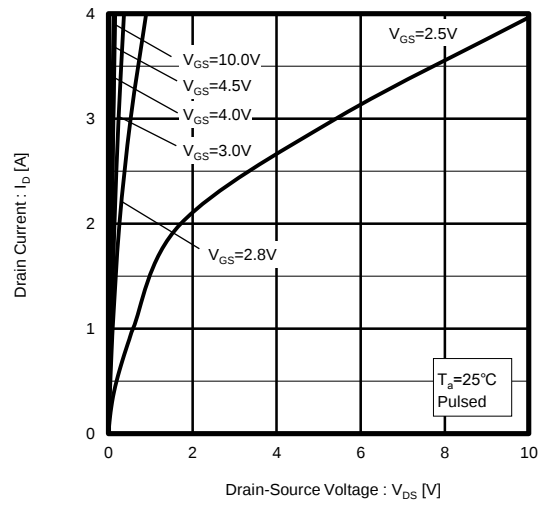


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

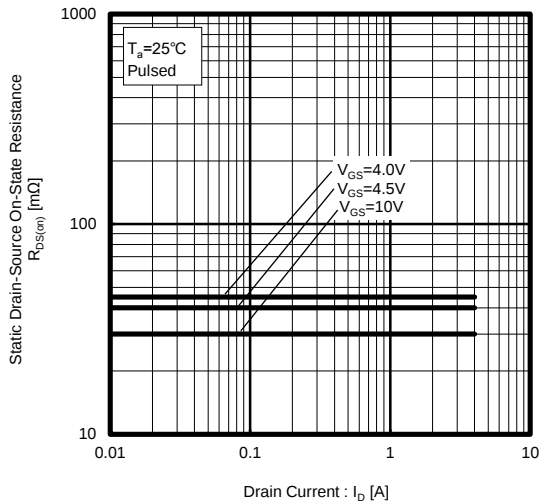


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

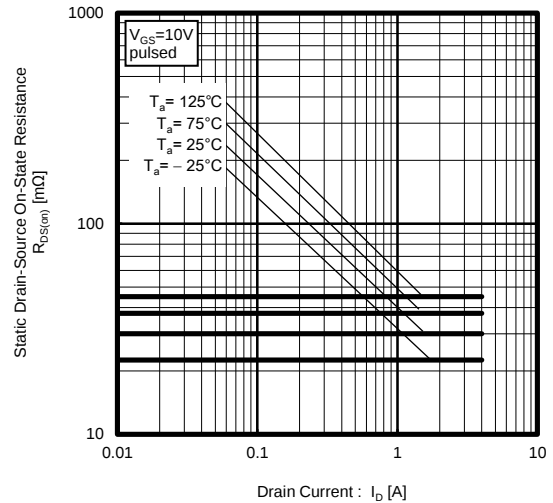


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

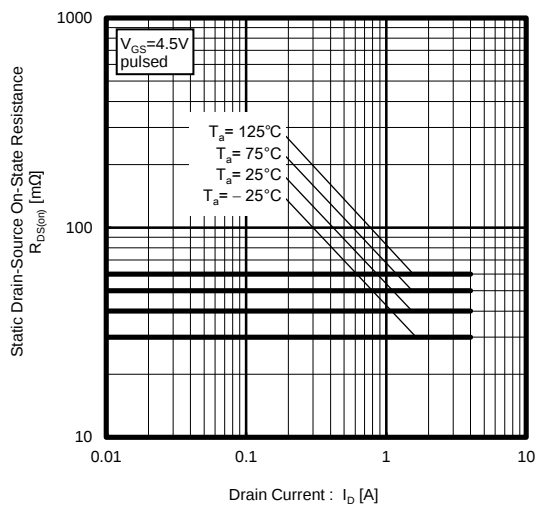


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

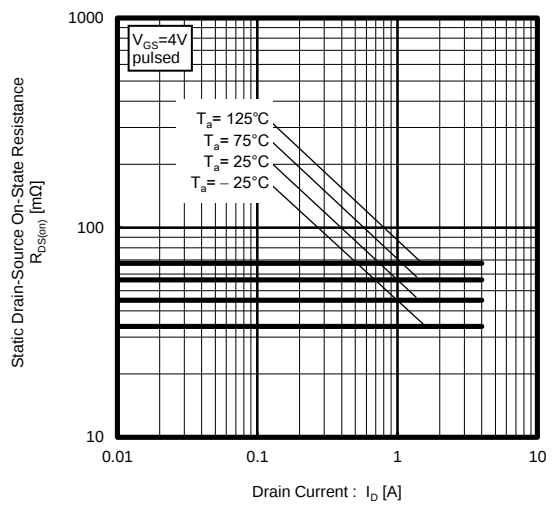


Fig.7 Forward Transfer Admittance vs. Drain Current

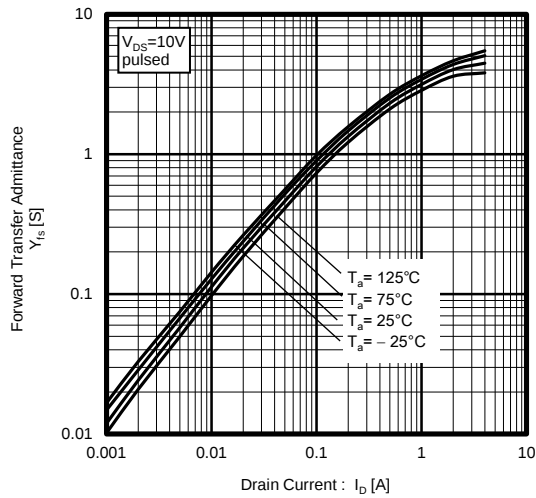


Fig.8 Typical Transfer Characteristics

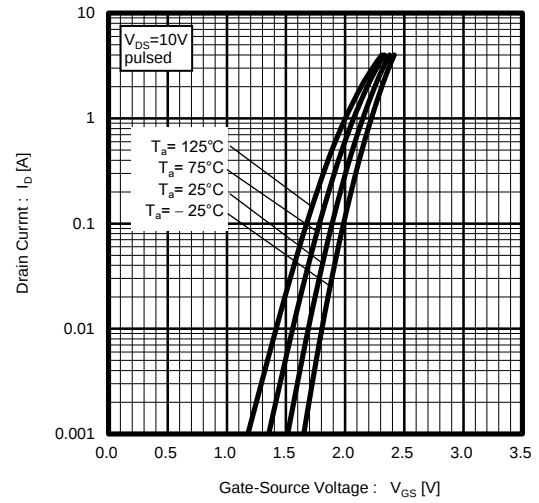


Fig.9 Source Current vs. Source-Drain Voltage

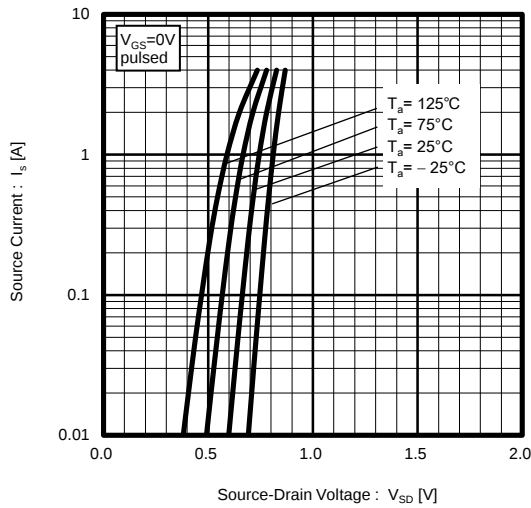


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

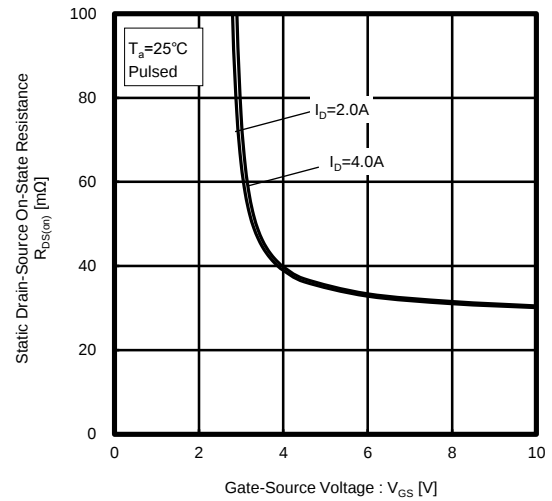


Fig.11 Switching Characteristics

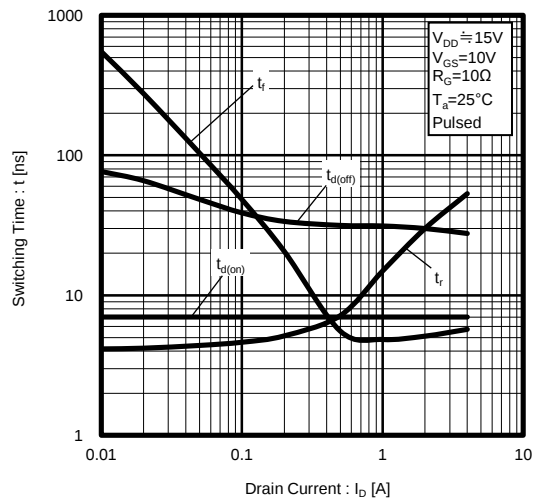


Fig.12 Dynamic Input Characteristics

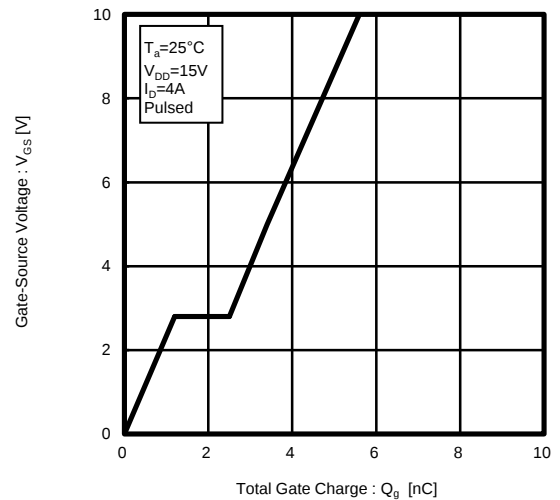


Fig.13 Typical Capacitance vs. Drain-Source Voltage

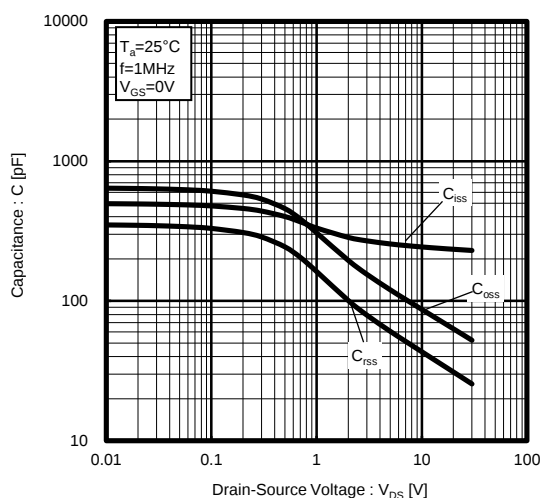


Fig.14 Maximum Safe Operating Area

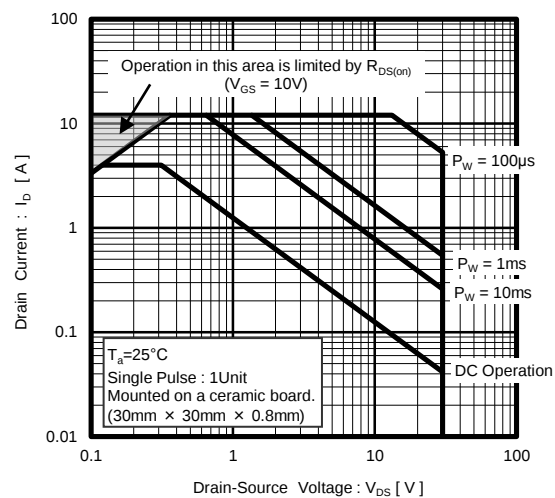
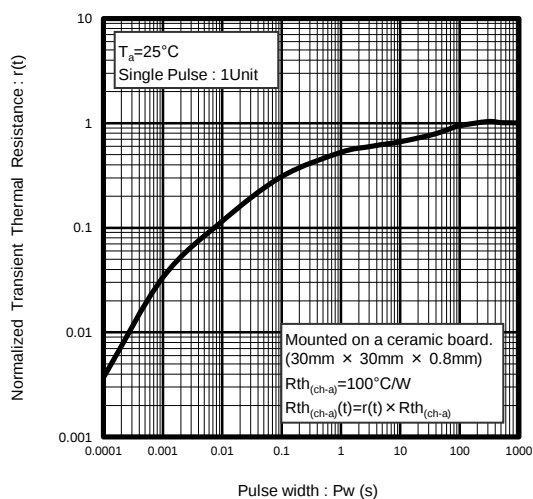


Fig.15 Normalized Transient Thermal Resistance v.s. Pulse Width



〈Tr.2(Pch)〉

Fig.1 Typical Output Characteristics (I)

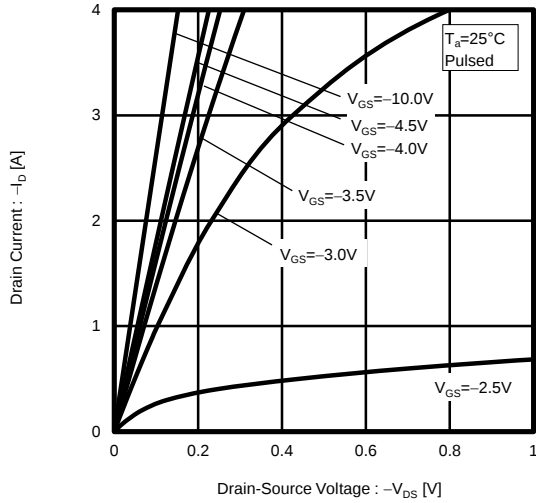


Fig.2 Typical Output Characteristics (II)

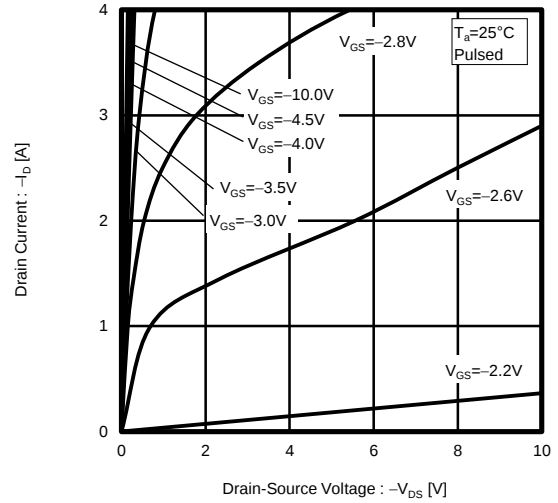


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

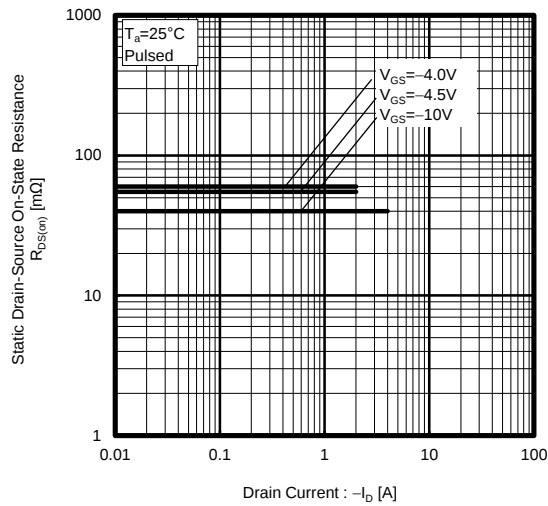


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

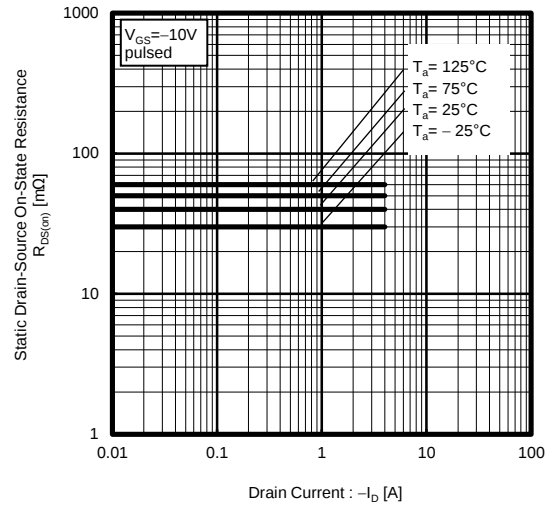


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

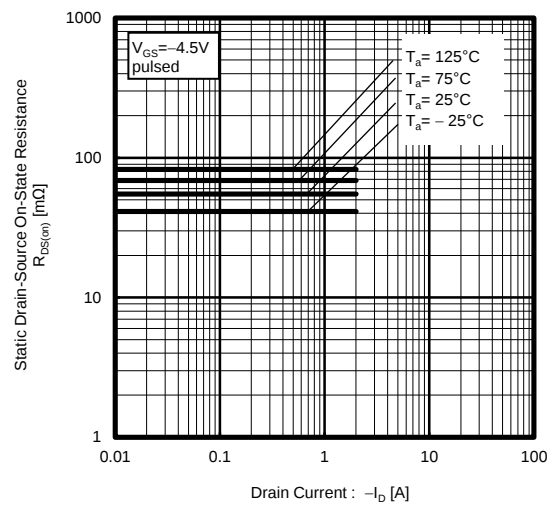


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

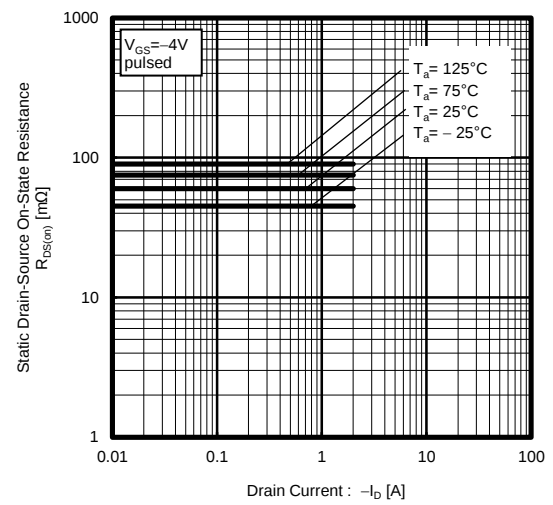


Fig.7 Forward Transfer Admittance vs. Drain Current

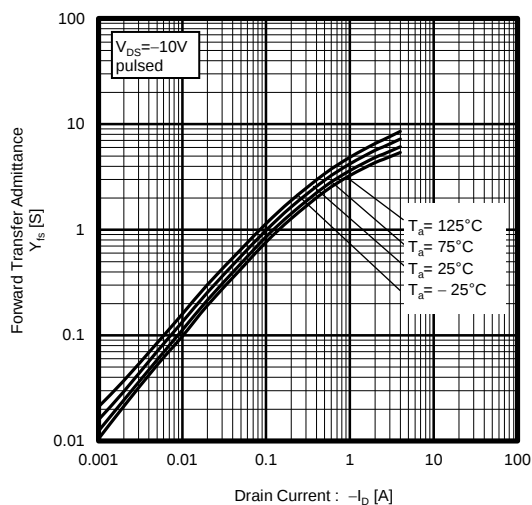


Fig.8 Typical Transfer Characteristics

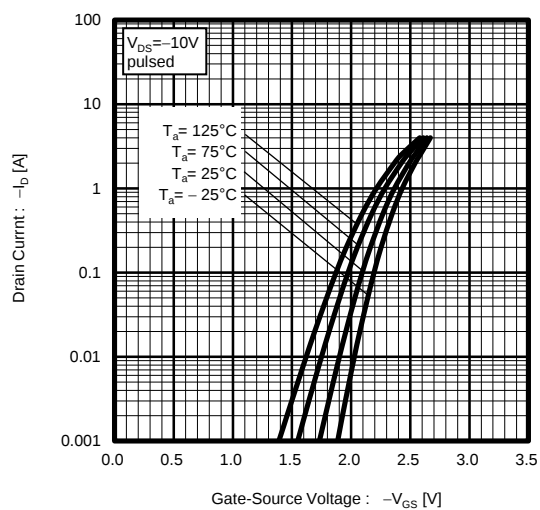


Fig.9 Source Current vs. Source-Drain Voltage

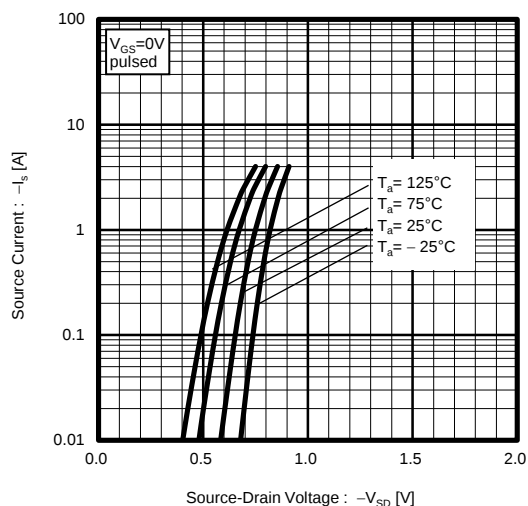


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

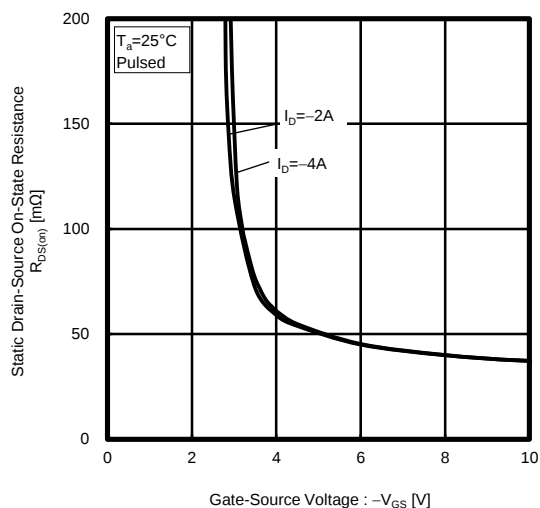


Fig.11 Switching Characteristics

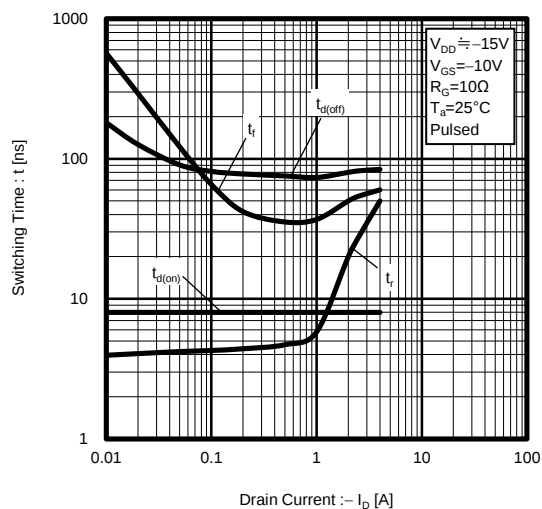


Fig.12 Dynamic Input Characteristics

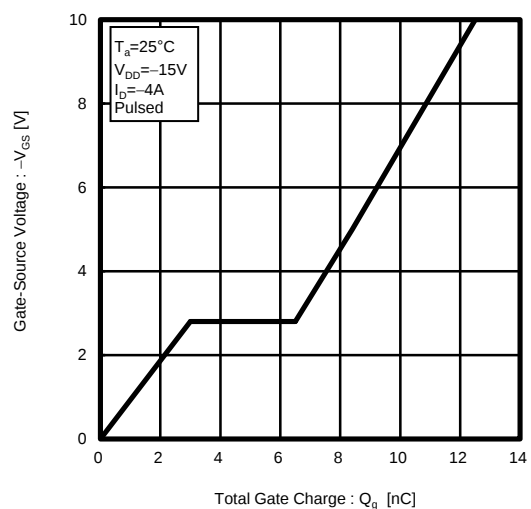


Fig.13 Typical Capacitance vs. Drain-Source Voltage

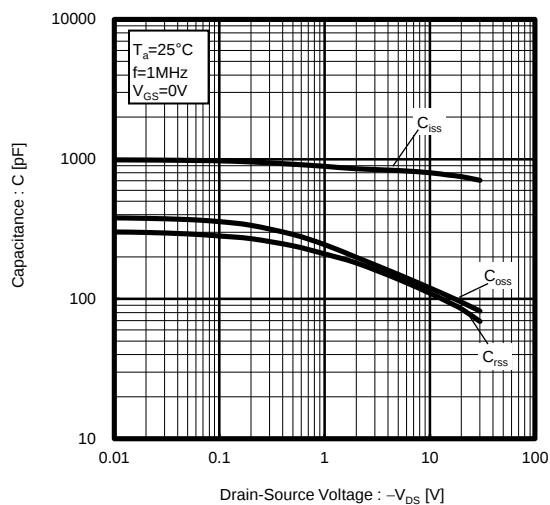


Fig.14 Maximum Safe Operating Area

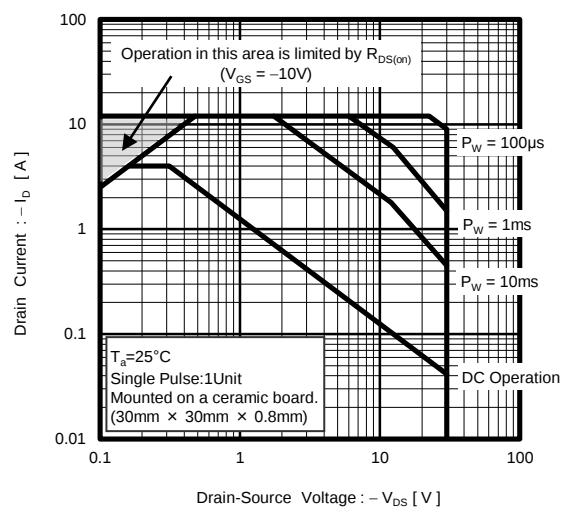
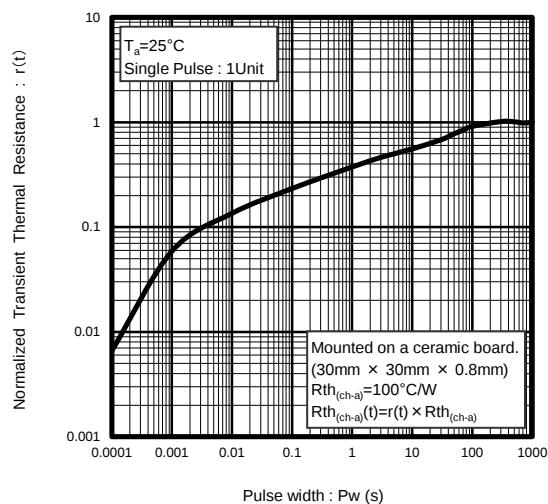


Fig.15 Normalized Transient Thermal Resistance v.s. Pulse Width



● Measurement circuits

<Tr1(Nch)>

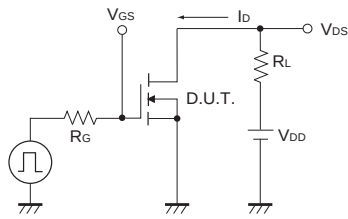


Fig.1-1 Switching Time Measurement Circuit

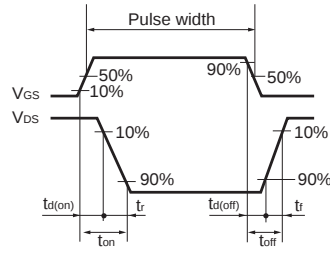


Fig.1-2 Switching Waveforms

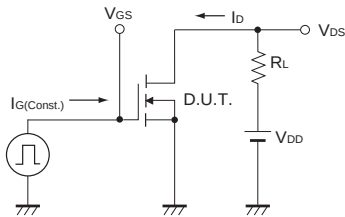


Fig.2-1 Gate Charge Measurement Circuit

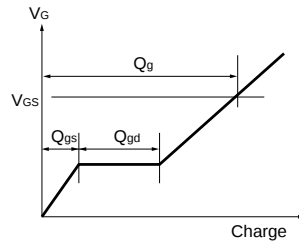


Fig.2-2 Gate Charge Waveform

<Tr2(Pch)>

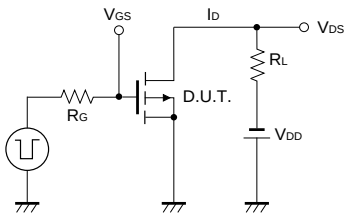


Fig.1-1 Switching Time Measurement Circuit

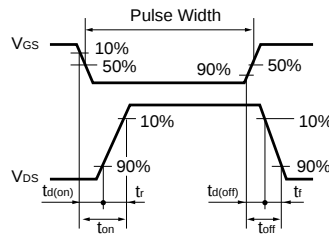


Fig.1-2 Switching Waveforms

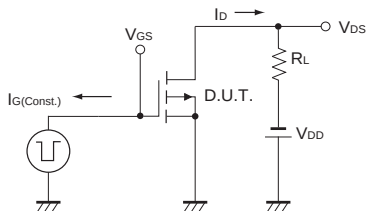


Fig.2-1 Gate Charge Measurement Circuit

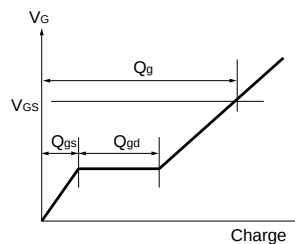


Fig.2-2 Gate Charge Waveform

● Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

Notes

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